INTEGRATED CIRCUITS

DATA SHEET

74F670

4 x 4 register file (3-State)

Product specification

1990 Jul 12

IC15 Data Handbook





4 x 4 register file (3-State)

74F670

FEATURES

- Simultaneous and Independent Read and Write operations
- Expandable to almost any word size and bit length
- 3-State outputs

DESCRIPTION

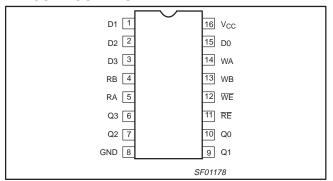
The 74F670 is a 16-bit 3-State Register File organized as 4 words of 4 bits each. Separate Read and Write Address and Enable inputs are available, permitting simultaneous writing into one word location and reading from another location. The 4-bit word to be stored is presented to four data inputs.

The Write address inputs (WA and WB) determine the location of the stored word. The Write Address inputs should only be changed when the Write Enable input ($\overline{\text{WE}}$) is High for conventional operation. When the $\overline{\text{WE}}$ is Low, the data is entered into the addressed location.

The addressed location remains transparent to the data while the \overline{WE} is Low. Data supplied at the inputs will be read out in true (non-inverting) form from the 3-State outputs. Data and address inputs are inhibited when the \overline{WE} is High. Direct acquisition of data stored in any of the four registers is made possible by individual Read Address inputs (RA, RB). The addressed word appears at the four outputs when the Read Enable (\overline{RE}) is Low. Data outputs are in the high impedance "off" state when the \overline{RE} is High. This permits outputs to be tied together to increase the word capacity to very large numbers.

Up to 128 devices can be stacked to increase the word size to 512 locations by tying the 3-State outputs together. Since the limiting factor for expansion is the output High current, further stacking is possible by tying pullup reisistors to the outputs to increase the $\rm I_{OH}$ current available. Design of the Read Enable signals for the stacked devices must ensure that there is no overlap in the Low levels which cause more than one output to be active at the same time. Parallel expansion to generate n-bit words is accomplished by driving the Enable and address inputs of each device in parallel.

PIN CONFIGURATION



	TYPE	TYPICAL PROPAGATION DELAY	TYPICAL SUPPLY CURRENT (TOTAL)
Ī	74F670	6.5ns	50mA

ORDERING INFORMATION

DESCRIPTION	COMMERCIAL RANGE V_{CC} = 5V $\pm 10\%$, T_{amb} = 0°C to +70°C	PKG DWG #
16-pin plastic DIP	N74F670N	SOT38-4
16-pin plastic SOL	N74F670D	SOT162-1

INPUT AND OUTPUT LOADING AND FAN-OUT TABLE

PINS	DESCRIPTION	74F(U.L.) HIGH/LOW	LOAD VALUE HIGH/LOW
D0 - D3	Data inputs	1.0/1.0	20μA/0.6mA
WA, WB	Write address inputs	1.0/1.0	20μA/0.6mA
RA, RB	Read address inputs	1.0/1.0	20μA/0.6mA
WE	Write Enable inputs	1.0/1.0	20mA/0.6mA
RE	Read Enable inputs	1.0/1.0	20mA/0.6mA
Q0-Q3	Data output	150/40	3.0mA/24mA

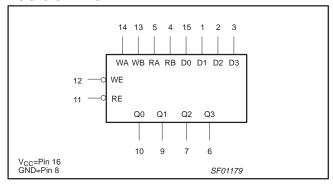
NOTE:

One (1.0) FAST Unit Load is defined as: $20\mu\text{A}$ in the High state and 0.6mA in the Low state.

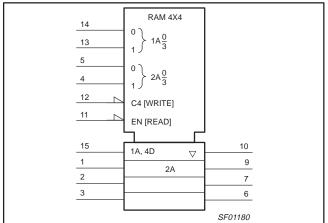
4 x 4 register file (3-State)

74F670

LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



WORD SELECT FUNCTION TABLE

WRITE	MODE	READ	MODE	OPERATING MODE	
WB	WA	RB	RA	Word Selected	
L	L	L	L	Word 0	
L	Н	L	Н	Word 1	
Н	L	Н	L	Word 2	
Н	Н	Н	Н	Word 3	

H = High voltage level L = Low voltage level

READ MODE FUNCTION TABLE

INPUT	INTERNAL	OUTPUT	OPERATING MODE	
RE	LATCHES* Qn		OPERATING WODE	
L	L	L	Read	
L	Н	Н	Reau	
Н	Х	Z	Disabled	

H = High voltage level
L = Low voltage level

X = Don't care

Z = High impedance "off" state
* = The selection of "internal latches" by Read Address (RA and RB) are not constrained by WE or RE operation.

WRITE MODE FUNCTION TABLE

INP	UTS	INTERNAL	OPERATING MODE
WE	Dn	LATCHES*	OPERATING MODE
L	L	L	Write data
L	Н	Н	wille data
Н	Х	NC	Data latched

H = High voltage level L = Low voltage level NC= No change

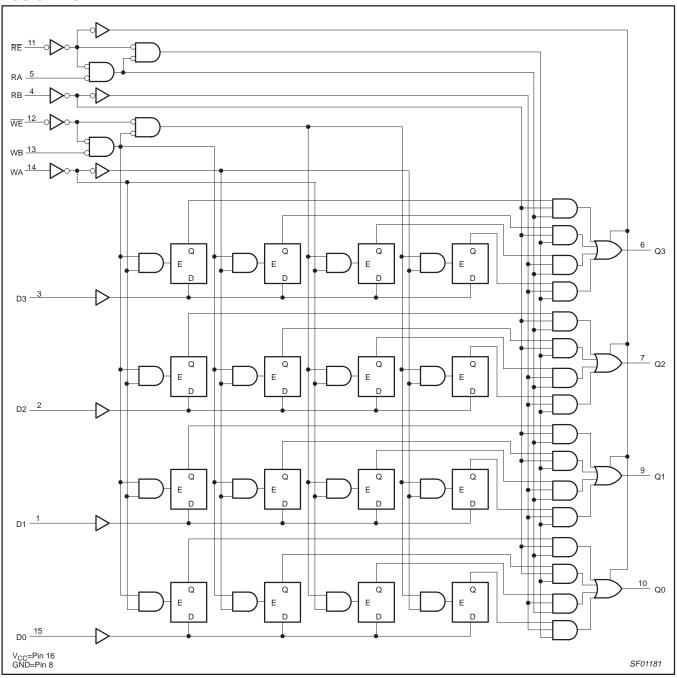
X = Don't care

The write address (WA and WB) to the "internal latches" must be stabled while WE is Low for conventional operation.

4 x 4 register file (3-State)

74F670

LOGIC DIAGRAM



4 x 4 register file (3-State)

74F670

ABSOLUTE MAXIMUM RATINGS

(Operation beyond the limits set forth in this table may impair the useful life of the device. Unless otherwise noted these limits are over the operating free-air temperature range.)

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	-0.5 to +7.0	V
V _{IN}	Input voltage	-0.5 to +7.0	V
I _{IN}	Input current	−30 to +5	mA
V _{OUT}	Voltage applied to output in High output state	–0.5 to V _{CC}	V
l _{OUT}	Current applied to output in Low output state	48	mA
T _{amb}	Operating free-air temperature range	0 to +70	°C
T _{stg}	Storage temperature	-65 to +150	°C

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER		UNIT		
STIVIBUL	FARAINETER	MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.0	5.5	V
V _{IH}	High-level input voltage	2.0			V
V _{IL}	Low-level input voltage			0.8	V
I _{IK}	Input clamp current			-18	mA
I _{OH}	High-level output current			-3	mA
I _{OL}	Low-level output current			24	mA
T _{amb}	Operating free-air temperature range	0		70	°C

DC ELECTRICAL CHARACTERISTICS

(Over recommended operating free-air temperature range unless otherwise noted.)

	PARAMETER						LIMITS		
SYMBOL			TEST CONDITIONS	MIN	TYP NO TAG	MAX	UNIT		
\ <u>'</u>	Lligh lovel output voltage		$V_{CC} = MIN, V_{IL} = MAX$	±10%V _{CC}	2.4			V	
V _{OH}	High-level output voltage		$V_{IH} = MIN, I_{OH} = MAX$	±5%V _{CC}	2.7	3.4		V	
V	o Low-level output voltage		$V_{CC} = MIN, V_{IL} = MAX$	±10%V _{CC}		0.35	0.50	V	
VOL			$V_{IH} = MIN, I_{OL} = MAX$	±5%V _{CC}		0.35	0.50	V	
V _{IK}	Input clamp voltage		$V_{CC} = MIN, I_I = I_{IK}$			-0.73	-1.2	V	
I _I	Input current at maximum input voltage		$V_{CC} = MAX, V_I = 7.0V$				100	μΑ	
I _{IH}	High-level input current		$V_{CC} = MAX, V_I = 2.7V$				20	μΑ	
I _{IL}	Low-level input current		$V_{CC} = MAX, V_I = 0.5V$				-0.6	mA	
I _{OZH}	Off state output current, High-level voltage applied		$V_{CC} = MAX, V_O = 2.7V$				50	μΑ	
I _{OZL}	Off state output current, Low-level voltage applied		$V_{CC} = MAX, V_O = 0.5V$				-50	μΑ	
Ios	Short-circuit output current ^{NO TAG}		V _{CC} = MAX		-60		-150	mA	
		I _{CCH}				50	70	mA	
I _{CC}	Supply current (total)	I _{CCL}	V _{CC} = MAX			50	70	mA	
	I _{CCZ}					55	80	mA	

NOTES:

- 1. For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- All typical values are at V_{CC} = 5V, T_{amb} = 25°C.
 Not more than one output should be shorted at a time. For testing I_{OS}, the use of high-speed test apparatus and/or sample-and-hold techniques are preferable in order to minimize internal heating and more accurately reflect operational values. Otherwise, prolonged shorting

4 x 4 register file (3-State)

74F670

of a High output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

AC ELECTRICAL CHARACTERISTICS

				LIMITS					
SYMBOL	PARAMETER TEST CONDITION		$T_{amb} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50pF,$ $R_{L} = 500\Omega$			$\begin{array}{c} \text{T}_{amb} = 0^{\circ}\text{C to } +70^{\circ}\text{C} \\ \text{V}_{CC} = +5.0\text{V} \pm 10\% \\ \text{C}_{L} = 50\text{pF}, \\ \text{R}_{L} = 500\Omega \end{array}$		UNIT	
			MIN	TYP	MAX	MIN	MAX	1	
t _{PLH} t _{PHL}	Propagation delay RA, RB to Qn	Waveform 3, 4	3.5 4.0	5.5 5.5	9.0 8.5	3.0 3.5	10.0 9.9	ns ns	
t _{PLH} t _{PHL}	Propagation delay WE to Qn	Waveform 1, 2	5.0 6.5	7.0 8.5	10.0 11.5	4.5 6.0	11.0 12.5	ns ns	
t _{PLH}	Propagation delay Dn to Qn	Waveform 1, 2	3.5 6.0	6.0 8.0	8.5 11.0	3.0 5.5	9.5 12.5	ns ns	
t _{PZH} t _{PZL}	RE Enable time Qn to High or Low level	Waveform 5 Waveform 6	3.0 4.5	7.0 6.5	12.0 9.0	2.5 4.0	13.0 10.0	ns ns	
t _{PHZ}	RE Disable time Qn to High or Low level	Waveform 5 Waveform 6	2.0 3.0	3.0 5.0	6.5 8.5	1.5 3.0	7.5 8.5	ns ns	

AC SETUP REQUIREMENTS

		TEST CONDITION						
SYMBOL	PARAMETER		V	_{imb} = +25° _{CC} = +5.0° 60pF, R _L =	V	T _{amb} = 0°0 V _{CC} = +5. C _L = 50pF,	UNIT	
			MIN	TYP	MAX	MIN	MAX	
$t_s(H)$ $t_s(L)$	Setup time, High or Low Dn to positive going WE	Waveform 3, 4	1.5 6.0			1.5 7.0		ns ns
t _h (H) t _h (L)	Hold time, High or Low Dn to positive going WE	Waveform 3, 4	0 1.0			0 1.0		ns ns
t _S (H) t _S (L)	Setup time, High or Low WA, WB to negative going WE ¹	Waveform 3, 4	0			0		ns ns
t _h (H) t _h (L)	Hold time, High or Low WA, WB to negative going WE ¹	Waveform 3, 4	0			0		ns ns
t _w (L)	WE Pulse width, Low	Waveform 3, 4	6.5			8.5		ns

NOTES:

^{1.} Write Address (WA, WB) setup time will protect the data written into the previous address. If protection of data in the previous address is not required, setup time for Write Address to WE can be ignored. Any address selection sustained for the final 7ns of the WE pulse during hold time for Write Address to WE will result in data being written into that location.

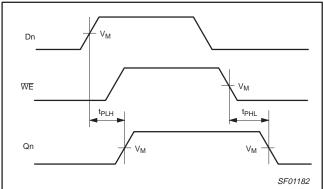
4 x 4 register file (3-State)

74F670

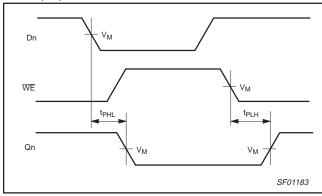
AC WAVEFORMS

For all waveforms, $V_M=1.5V$.

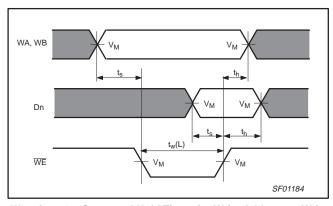
The shaded areas indicate when the input is permitted to change for predictable output performance.



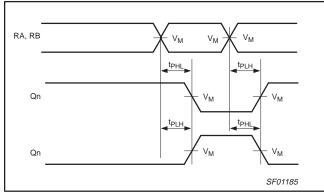
Waveform 1. Propagation Delay, Write Enable and Data to Outptus



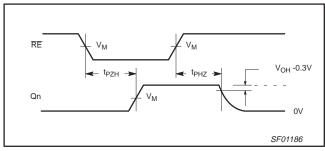
Waveform 2. Propagation Delay, Write Enable and Data to Outputs



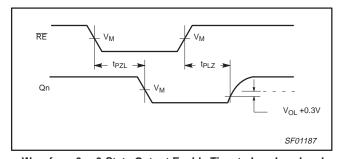
Waveform 3. Setup and Hold Times for Write Address to Write Enable and Data to Write Enable



Waveform 4. Propagation Delays for Read Address to Output



Waveform 5. 3-State Output Enable Time to High Level and Output Disable Time from High Level

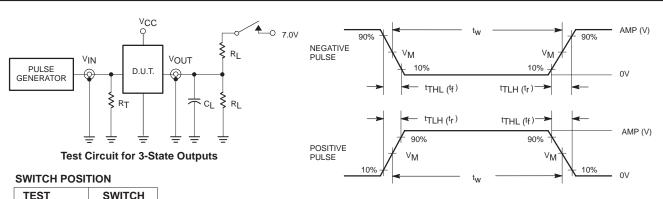


Waveform 6. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level

4 x 4 register file (3-State)

74F670

TEST CIRCUIT AND WAVEFORM



TEST	SWITCH
t _{PLZ}	closed
t _{PZL}	closed
All other	open

DEFINITIONS:

R_L = Load resistor;

see AC electrical characteristics for value.

C_L = Load capacitance includes jig and probe capacitance;

see AC electrical characteristics for value.

 $R_T = \mbox{Termination resistance should be equal to Z_{OUT} of pulse generators.}$

family	INPUT PULSE REQUIREMENTS								
lallilly	amplitude	V_{M}	rep. rate	t _w	t _{TLH}	t _{THL}			
74F	3.0V	1.5V	1MHz	500ns	2.5ns	2.5ns			

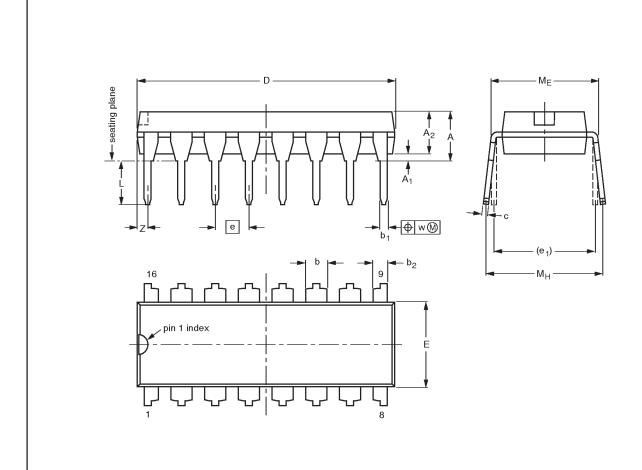
Input Pulse Definition

SF00777

Register file 74F670

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4





DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.030

Note

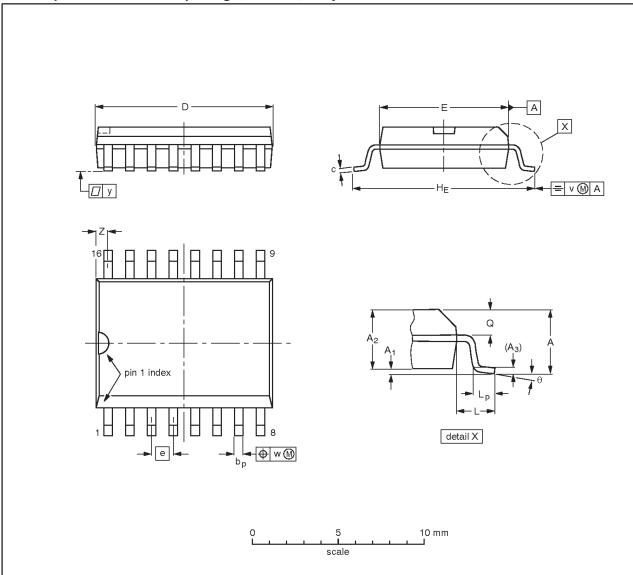
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT38-4				□ •	92-11-17 95-01-14

Register file 74F670

SO16: plastic small outline package; 16 leads; body width 7.5 mm

SOT162-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	Ьp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	10.5 10.1	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.41 0.40	0.30 0.29	0.050	0.419 0.394	0.055		0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT162-1	075E03	MS-013AA			95 01 24 97-05-22

Register file 74F670

NOTES

Register file 74F670

Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

^[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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